# Zibo Seno Electronic Engineering Co., Ltd.



# **MBR1640CT – MBR16200CT**



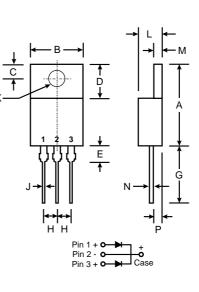
### **16.0A SCHOTTKY BARRIER DIODE**

#### Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O

#### **Mechanical Data**

- Case: TO-220AB, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Mounting Position: Any
- Lead Free: For RoHS / Lead Free Version



TO-220AB							
Dim	Min	Max					
Α	14.22	15.88					
В	9.57	10.57					
С	2.54	3.43					
D	5.80	6.80					
E		6.35					
G	12.70	14.73					
Н	2.29	2.79					
J	0.51	1.14					
к	3.53Ø	4.14Ø					
L	3.56	4.83					
м	1.07	1.47					
N	0.30	0.64					
Р	2.03	2.92					
All Dimensions in mm							

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### Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR 1640 CT	MBR 1645 CT	MBR 1650 CT	MBR 1660 CT	MBR 16100 CT	MBR 16150 CT	MBR 16200 CT	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	40	45	50	60	100	150	200	V
RMS Reverse Voltage	VR(RMS)	28	31	35	42	70	105	140	V
Average Rectified Output Current $@T_L = 75^{\circ}C$ (Note 1)	lo	16.0					A		
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	120					A		
Forward Voltage $@I_F = 8A$	Vfm	0.70		0.80		0.85	0.92		V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	Irm	0.1 20						mA	
Typical Junction Capacitance (Note 2)	Cj	350		280		200		pF	
Typical Thermal Resistance (Note 1)	RθJA	3.5			2.0			°C/W	
Operating and Storage Temperature Range	Tj, Tstg	-55 to +150			-55 to +175		°C		

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case. 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

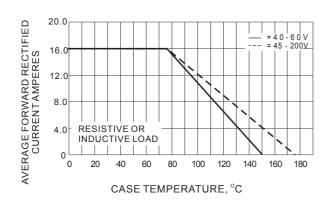
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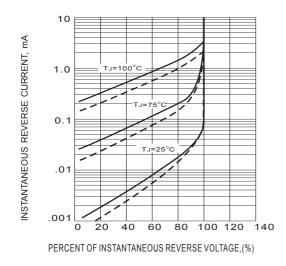
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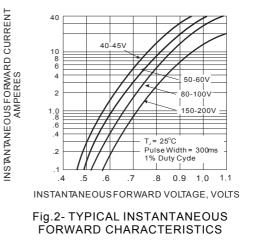
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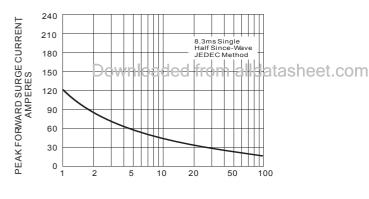




Fig.4- MAXIMUM NON - REPETITIVE SURGE CURRENT

ΑL

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